

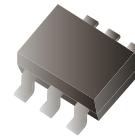
Small Surface Mount Transistor

Comchip
SMD Diode Specialist

ABC846BPN-HF (NPN PNP)

RoHS Device

Halogen Free



Features

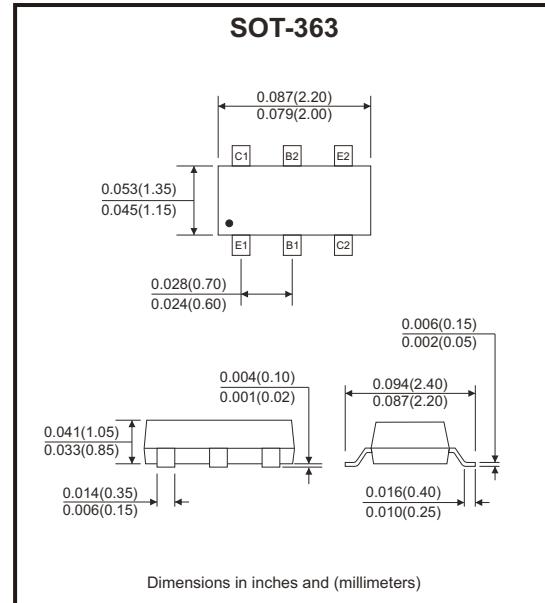
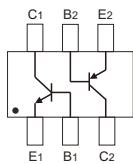
- Low collector capacitance.
- Low collector-emitter saturation voltage.
- Reduces number of components and board space.
- No mutual interference between the transistors.
- AEC-Q101 Qualified.

Mechanical data

- Case: SOT-363, molded plastic.

Circuit Diagram

B :Base
E :Emitter
C :Collector



Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	NPN	PNP	Unit
Collector-base voltage	V _{CBO}	80	-80	V
Collector-emitter voltage	V _{CEO}	65	-65	V
Emitter-base voltage	V _{EBO}	6	-6	V
Collector current-continuous	I _C	100	-100	mA
Collector current-peak	I _{CM}	200	-200	mA
Base current-peak	I _{BM}	200	-200	mA
Power dissipation	P _D	200		mW
Thermal resistance, junction to ambient	R _{θJA}	625		°C/W
Ambient temperature range	T _{amb}	-55 to +150		°C
Junction and storage temperature range	T _J , T _{STG}	-65 to +150		°C

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Electrical Characteristics of TR1 NPN Transistor (Ta= 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10µA, I _E = 0	80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, I _B = 0	65			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10µA, I _C = 0	6			V
Collector cut-off current	I _{CBO}	V _{CB} = 50V, I _E = 0			15	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 6V, I _C = 0			100	nA
DC current gain	h_{FE}	V _{CE} = 5V, I _C = 10µA		280		
		V _{CE} = 5V, I _C = 2mA	200	290	450	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5mA		0.05 0.2	0.1 0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5mA		0.755 1	0.85 -	V
Base-emitter voltage	V _{BE(on)}	V _{CE} = 5V, I _C = 2mA V _{CE} = 5V, I _C = 10mA	0.58 -	0.65 -	0.7 0.77	V
Transition frequency	f _T	V _{CE} = 5V, I _C = 10mA, f = 100MHz	100			MHz
Collector capacitance	C _c	V _{CB} = 10V, f = 1MHz		1.9		pF
Emitter capacitance	C _e	V _{CB} = 0.5V, f = 1MHz		11		pF

Electrical Characteristics of TR2 PNP Transistor (Ta= 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10µA, I _E = 0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B = 0	-65			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10µA, I _C = 0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = -50V, I _E = 0			-15	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -6V, I _C = 0			-100	nA
DC current gain	h_{FE}	V _{CE} = -5V, I _C = -10µA		280		
		V _{CE} = -5V, I _C = -2mA	200	290	450	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5mA		-0.055 -0.2	-0.1 -0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5mA		-0.755 -0.9	-0.85 -	V
Base-emitter on voltage	V _{BE(on)}	V _{CE} = -5V, I _B = -2mA V _{CE} = -5V, I _B = -10mA	-0.6 -	-0.65 -	-0.75 -0.82	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA, f = 100MHz	100			MHz
Collector capacitance	C _c	V _{CB} = -10V, f = 1MHz		2.3		pF
Emitter capacitance	C _e	V _{CB} = -0.5V, f = 1MHz		10		pF

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Rating and Characteristic Curves (ABC846BPN-HF)

Fig.1 - TR1 (NPN): DC Current Gain as a Function of Collector Current; Typical Values

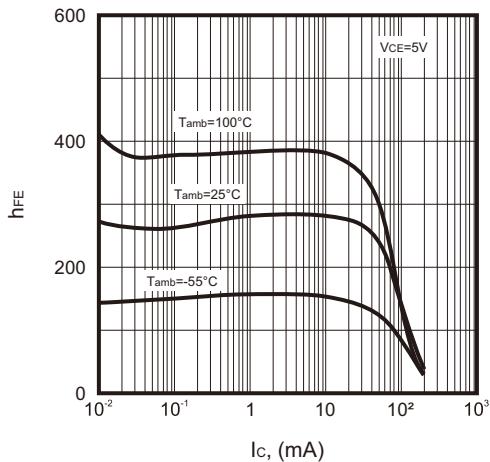


Fig.2 - TR1 (NPN): Collector Current as a Function of Collector-Emitter Voltage; Typical Values

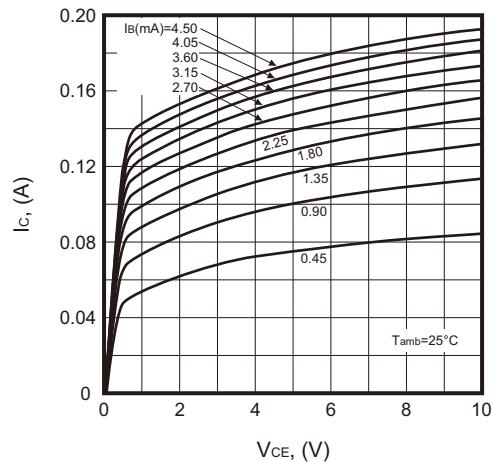


Fig.3 - TR1 (NPN): Base-Emitter Voltage as a Function of Collector Current; Typical Values

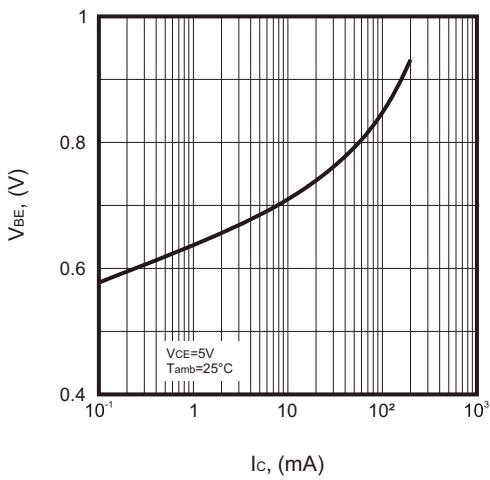


Fig.4 - TR1 (NPN): Base-Emitter Saturation Voltage as a Function of Collector Current; Typical Values

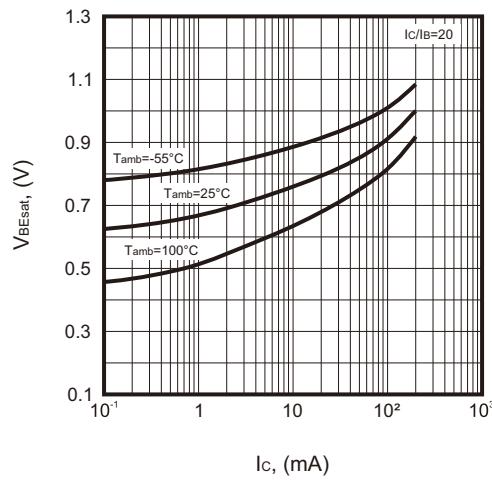


Fig.5 - TR1 (NPN): Collector-Emitter Saturation Voltage as a Function of Collector Current; Typical Values

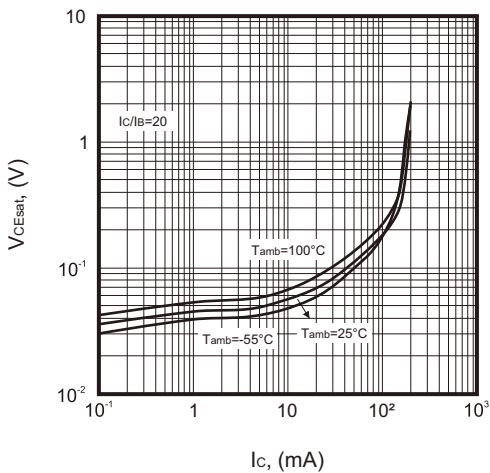
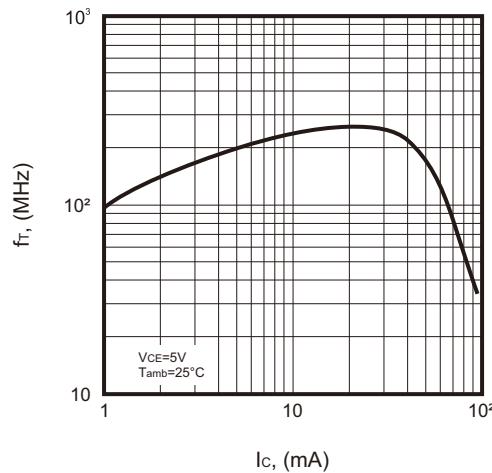


Fig.6 - TR1 (NPN): Transition Frequency as a Function of Collector Current; Typical Values



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Rating and Characteristic Curves (ABC846BPN-HF)

Fig.7 - TR2 (PNP): DC Current Gain as a Function of Collector Current; Typical Values

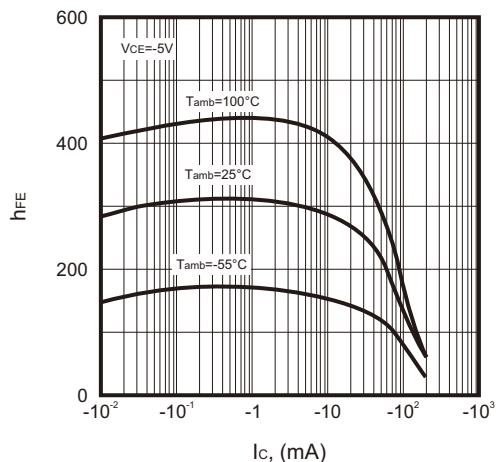
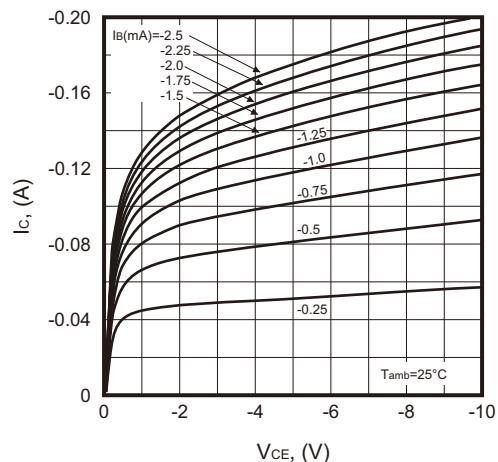


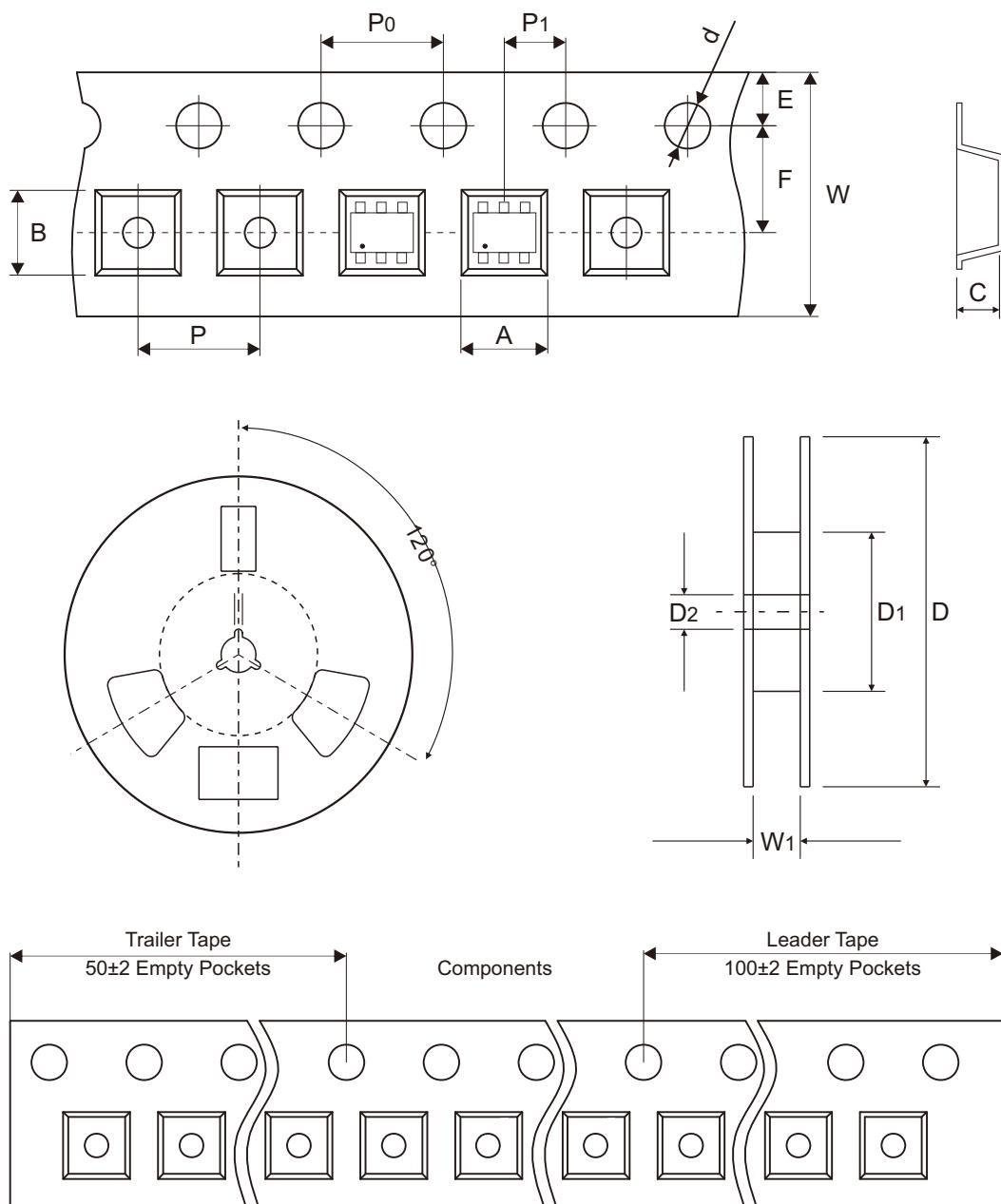
Fig.8 - TR2 (PNP): Collector Current as a Function of Collector-Emitter Voltage; Typical Values



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Reel Taping Specification



SOT-363	SYMBOL	A	B	C	d	D	D ₁	D ₂
	(mm)	2.40 ± 0.10	2.40 ± 0.10	1.20 ± 0.10	1.50 ± 0.10	178.00 ± 1.00	54.00 ± 0.50	13.00 ± 0.50
	(inch)	0.094 ± 0.004	0.094 ± 0.004	0.047 ± 0.004	0.059 ± 0.004	7.008 ± 0.039	2.126 ± 0.020	0.512 ± 0.020

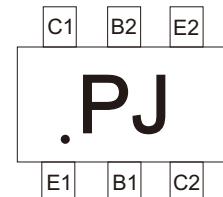
SOT-363	SYMBOL	E	F	P	P ₀	P ₁	W	W ₁
	(mm)	1.75 ± 0.10	3.50 ± 0.05	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	8.00 ± 0.30 -0.10	9.50 ± 1.00
	(inch)	0.069 ± 0.004	0.138 ± 0.002	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.315 ± 0.012 -0.004	0.374 ± 0.039

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Marking Code

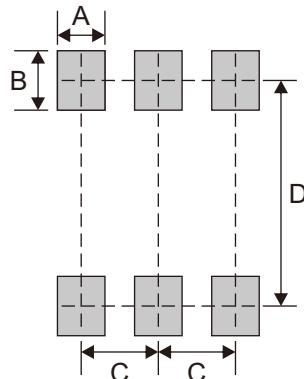
Part Number	Marking Code
ABC846BPN-HF	PJ



Solid dot “ • ” = Pin 1 indicate.

Suggested P.C.B. PAD Layout

SIZE	SOT-363	
	(mm)	(inch)
A	0.40	0.016
B	0.50	0.020
C	0.65	0.026
D	1.90	0.075



Note: 1. The pad layout is for reference purposes only.

Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-363	3,000	7

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